ChunZheng

High-end Power Semiconductor Manufacturer

KP250A 4600V-6500V

Phase Control Thyristor

- High power cycling capability
- Low on-state and switching losses
- Designed for traction and industrial applications

Mean on-state current					I_{TAV}		250 A				
Repetitive peak off-state voltage					V_{DRM}		4600 – 6500 V				
Repetitive peak reverse voltage					V_{RRM}						
Turn-off time					t_q		630 μs				
V_{DRM}, V_{RRM}, V	4600	4800	5000	5200	5400	5600	5800	6000	6200	6400	6500
Voltage code	46	48	50	52	54	56	58	60	62	64	65
T_j, °C	-60 – 125										

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{TAV}	Mean on-state current	A	250	T_c=85 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I_{TRMS}	RMS on-state current	A	392.5	T_c=85 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I_{TSM}	Surge on-state current	kA	4.5 5.0	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; 50 Hz (t_p=10 ms); single pulse; V_D=V_R=0 V; Gate pulse: I_G=2 A; t_{GP}=50 μs; di_G/dt≥1 A/μs
			5.0 6.0	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; 60 Hz (t_p=8.3 ms); single pulse; V_D=V_R=0 V; Gate pulse: I_G=2 A; t_{GP}=50 μs; di_G/dt≥1 A/μs
I^2t	Safety factor	$A^2s{\cdot}10^3$	100 125	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; 50 Hz (t_p=10 ms); single pulse; V_D=V_R=0 V; Gate pulse: I_G=2 A; t_{GP}=50 μs; di_G/dt≥1 A/μs
			125 145	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; 60 Hz (t_p=8.3 ms); single pulse; V_D=V_R=0 V; Gate pulse: I_G=2 A; t_{GP}=50 μs; di_G/dt≥1 A/μs
BLOCKING					
V_{DRM}, V_{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	4600–6500	$T_{j\,min}$< T_j <$T_{j\,max}$; 180° half-sine wave; 50 Hz; Gate open	
V_{DSM}, V_{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	4700–6600	$T_{j\,min}$< T_j <$T_{j\,max}$; 180° half-sine wave; 50 Hz;single pulse; Gate open	
V_D, V_R	Direct off-state and Direct reverse voltages	V	0.75·V_{DRM} 0.75·V_{RRM}	T_j=$T_{j\,max}$; Gate open	

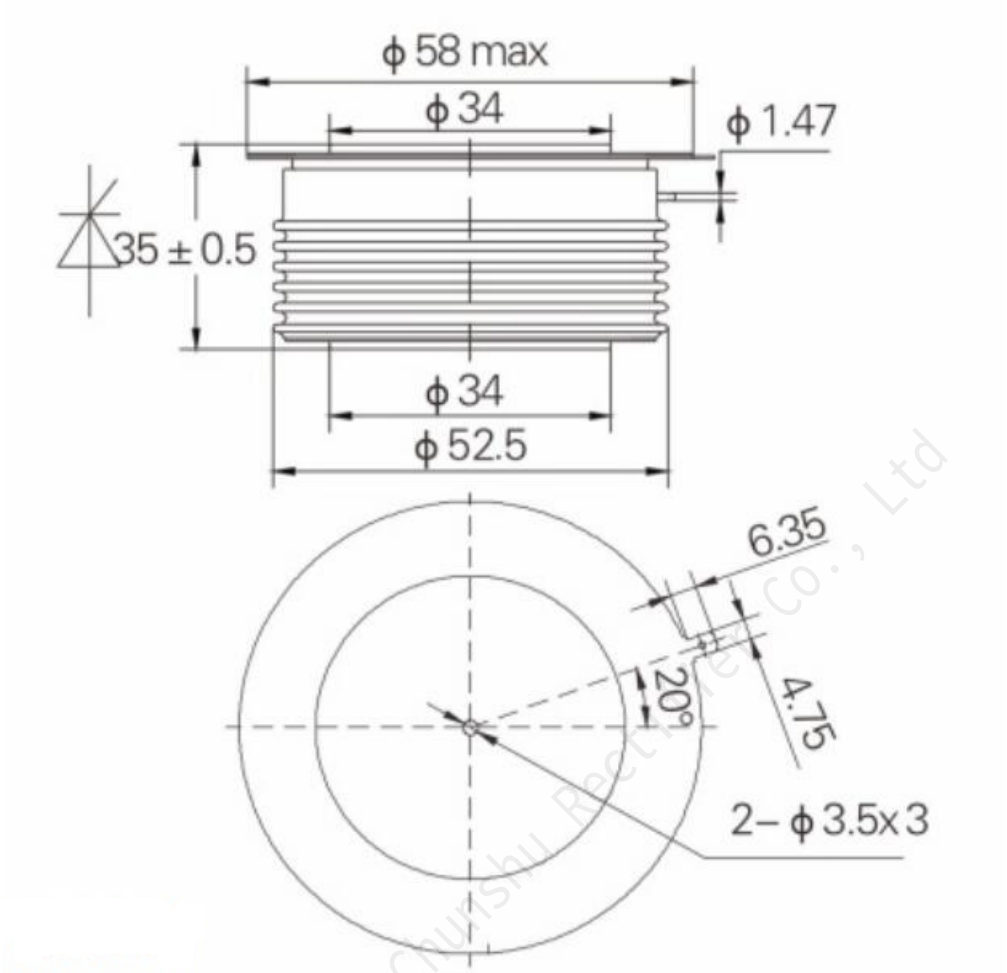
TRIGGERING				
I_{FGM}	Peak forward gate current	A	8	$T_j=T_{j\,max}$
V_{RGM}	Peak reverse gate voltage	V	5	
P_G	Gate power dissipation	W	4	$T_j=T_{j\,max}$ for DC gate current
SWITCHING				
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive (f=1 Hz)	A/μs	500	$T_j=T_{j\,max}$; $V_D=0.67\cdot V_{DRM}$; $I_{TM}=2\ I_{TAV}$; Gate pulse: $I_G=2$ A; $t_{GP}=50$ μs; $di_G/dt\geq 1$ A/μs
THERMAL				
T_{stg}	Storage temperature	°C	-60 – 125	
T_j	Operating junction temperature	°C	-60 – 125	
MECHANICAL				
F	Mounting force	kN	14.0 – 16.0	
a	Acceleration	m/s^2	50 100	Device unclamped Device clamped

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{TM}	Peak on-state voltage, max	V	2.90	$T_j=25$ °C; $I_{TM}=785$ A	
$V_{T(TO)}$	On-state threshold voltage, max	V	1.15	$T_j=T_{j\,max}$; $0.5\ \pi\ I_{TAV} < I_T < 1.5\ \pi\ I_{TAV}$	
r_T	On-state slope resistance, max	mΩ	2.520		
I_L	Latching current, max	mA	700	$T_j=25$ °C; $V_D=12$ V; Gate pulse: $I_G=2$ A; $t_{GP}=50$ μs; $di_G/dt\geq 1$ A/μs	
I_H	Holding current, max	mA	300	$T_j=25$ °C; $V_D=12$ V; Gate open	
BLOCKING					
I_{DRM}, I_{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	150	$T_j=T_{j\,max}$; $V_D=V_{DRM}$; $V_R=V_{RRM}$	
$(dv_D/dt)_{crit}$	Critical rate of rise of off-state voltage[1], min	V/μs	1000	$T_j=T_{j\,max}$; $V_D=0.67\cdot V_{DRM}$; Gate open	
TRIGGERING					
V_{GT}	Gate trigger direct voltage, max	V	2.50 2.00	$T_j=25$ °C $T_j=T_{j\,max}$	$V_D=12$ V; $I_D=3$ A; Direct gate current
I_{GT}	Gate trigger direct current, max	mA	300 200	$T_j=25$ °C $T_j=T_{j\,max}$	
V_{GD}	Gate non-trigger direct voltage, min	V	0.35	$T_j=T_{j\,max}$; $V_D=0.67\cdot V_{DRM}$; Direct gate current	
I_{GD}	Gate non-trigger direct current, min	mA	15.00		
SWITCHING					
t_{gd}	Delay time	μs	4.00	$T_j=25$ °C; $V_D=0.4\cdot V_{DRM}$; $I_{TM}=I_{TAV}$; Gate pulse: $I_G=2$ A; $t_{GP}=50$ μs; $di_G/dt\geq 1$ A/μs	
t_q	Turn-off time[2], max	μs	630	$dv_D/dt=50$ V/μs; $T_j=T_{j\,max}$; $I_{TM}=1000$ A; $di_R/dt=-10$ A/μs; $V_R=100$V; $V_D=2000$ V	
Q_{rr}	Total recovered charge, max	μC	3500	$T_j=T_{j\,max}$; $I_{TM}=1000$ A; $di_R/dt=-5$ A/μs; $V_R=100$ V	
t_{rr}	Reverse recovery time, typ	μs	50		
I_{rrM}	Peak reverse recovery current, max	A	140		

THERMAL					
R_{thjc}	Thermal resistance, junction to case, max	°C/W	0.0450	Direct current	Double side cooled
R_{thjc-A}			0.0990		Anode side cooled
R_{thjc-K}			0.0810		Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	°C/W	0.0075	Direct current	
MECHANICAL					
w	Weight, typ	g	400		
D_s	Surface creepage distance	mm (inch)	38.00 (1.496)		
D_a	Air strike distance	mm (inch)	21.00 (0.827)		

OVERALL DIMENSIONS



KT40DT

All dimensions in millimeters

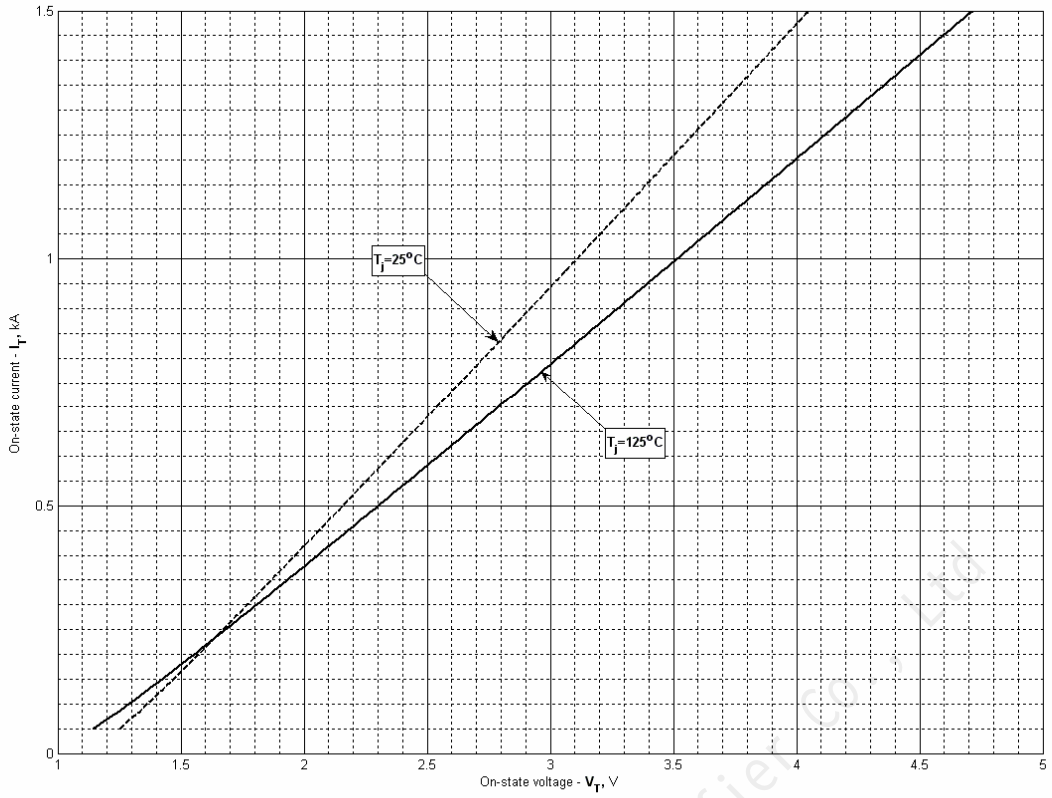


Fig 1 – On-state characteristics of Limit device

Analytical function for On-state characteristic:

$$V_T = A + B \cdot i_T + C \cdot \ln(i_T + 1) + D \cdot \sqrt{i_T}$$

	Coefficients for max curves	
	T_j = 25°C	$T_j = T_{j\,max}$
A	1.100009	0.947147
B	1.839506	2.342629
C	-0.218225	-0.291455
D	0.318651	0.425581

On-state characteristic model (see Fig. 1)

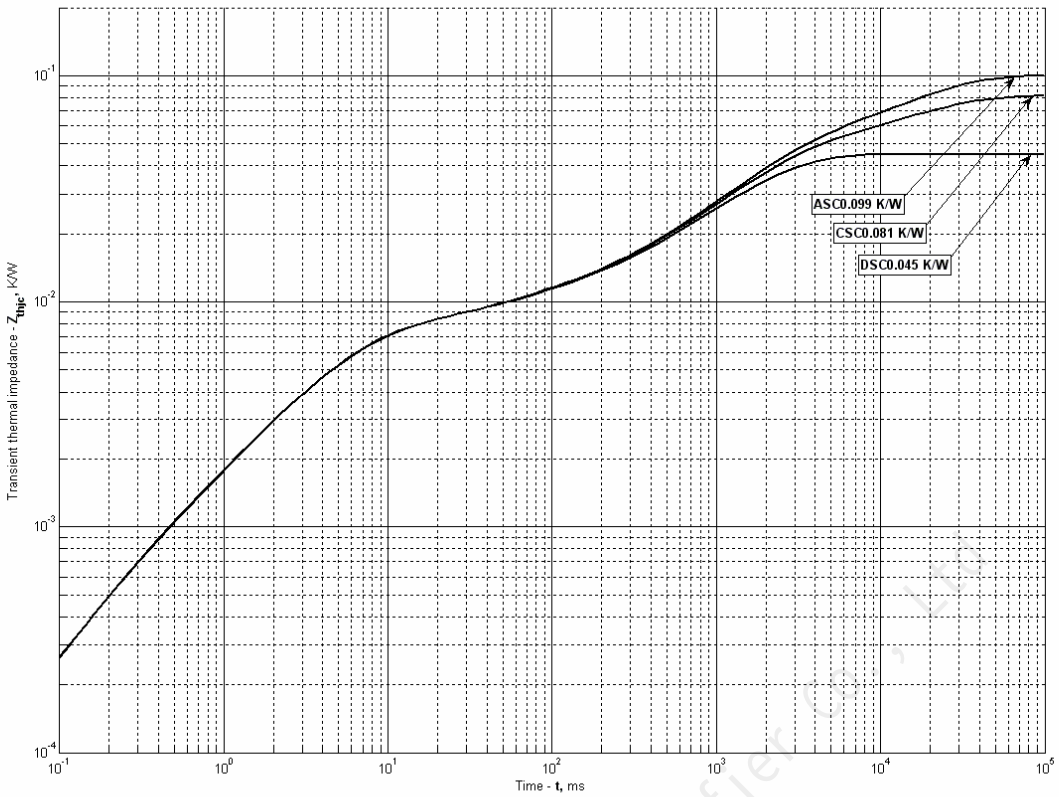


Fig 2 – Transient thermal impedance

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^{n} R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where ***i*** = 1 to ***n***, ***n*** is the number of terms in the series.

t = Duration of heating pulse in seconds.

$\mathbf{Z_{thjc}}$ = Thermal resistance at time t.

$\mathbf{R_i}$ = Amplitude of p_{th} term.

τ_i = Time constatnt of r_{th} term.

DC Double side cooled

i	1	2	3	4	5	6
$\mathbf{R_i}$, **K/W**	0.0003324	0.003816	0.00345	0.002093	0.001185	0.03412
τ_i, **s**	0.0002588	0.003593	0.006835	0.06337	0.4078	1.714

DC Cathode side cooled

i	1	2	3	4	5	6
$\mathbf{R_i}$, **K/W**	0.0004152	0.006772	0.001903	0.001399	0.03451	0.03653
τ_i, **s**	0.0003214	0.004599	0.03962	0.2053	1.810	17.69

DC Anode side cooled

i	1	2	3	4	5	6
$\mathbf{R_i}$, **K/W**	0.0004076	0.006732	0.001746	0.001465	0.03471	0.05539
τ_i, **s**	0.0003146	0.004563	0.03539	0.1651	1.871	17.71

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

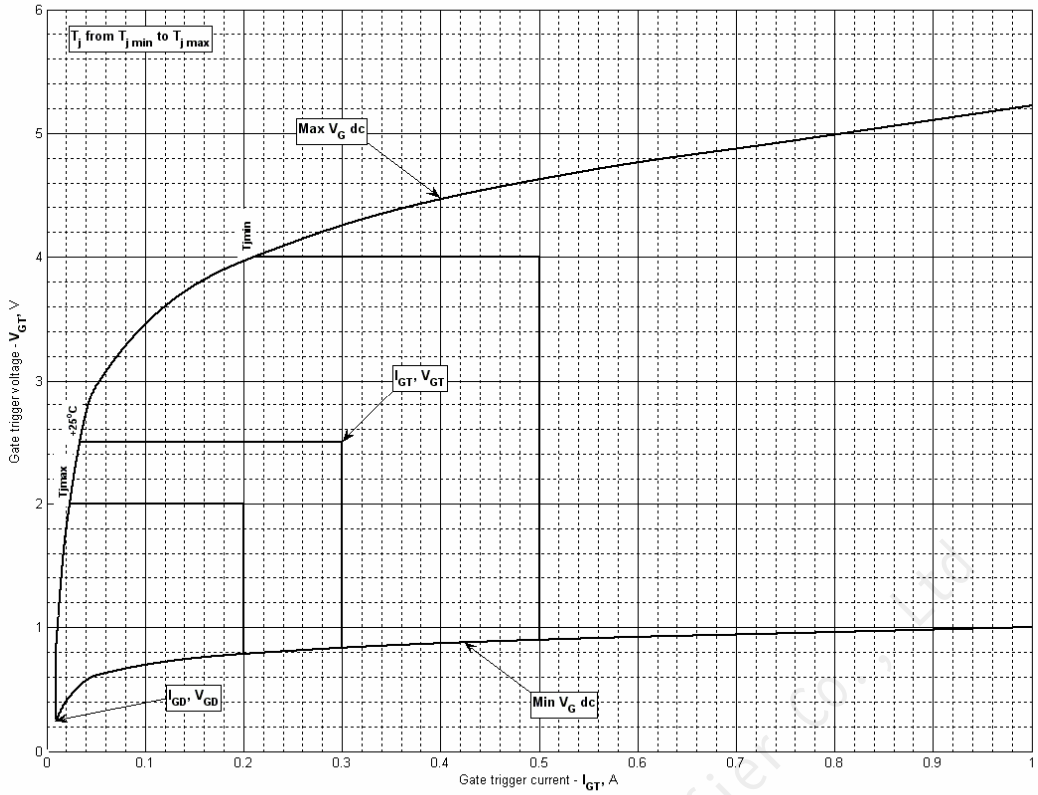


Fig 3 – Gate characteristics – Trigger limits

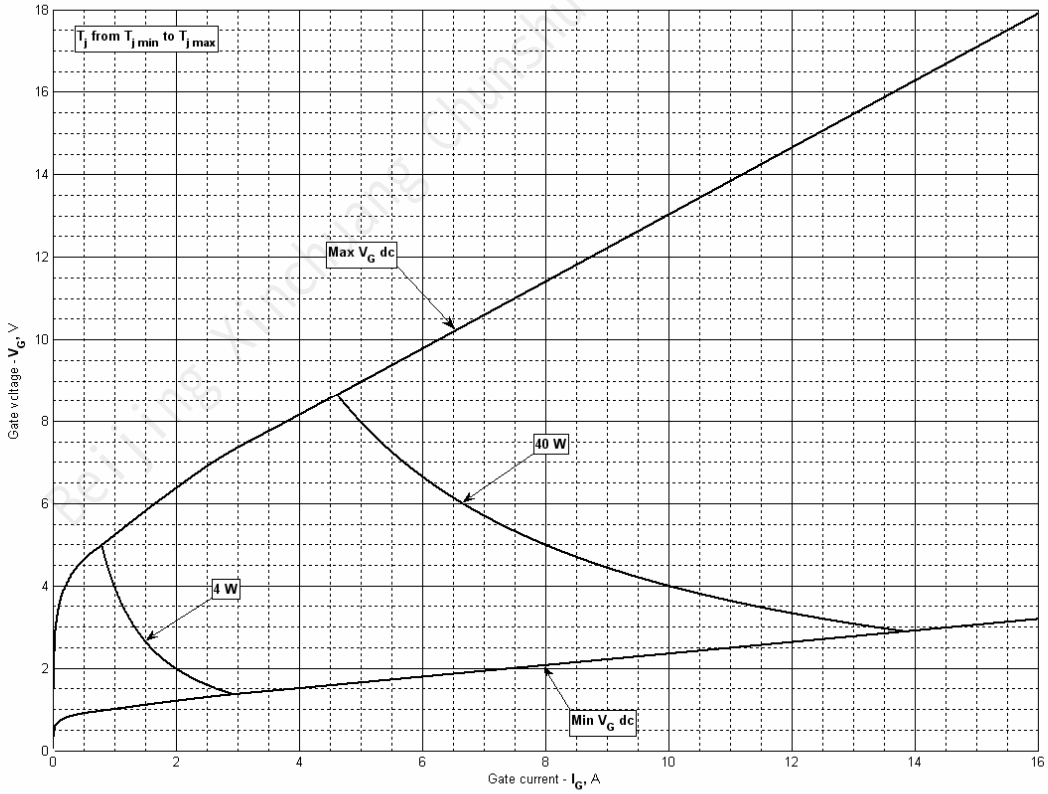


Fig 4 - Gate characteristics –Power curves

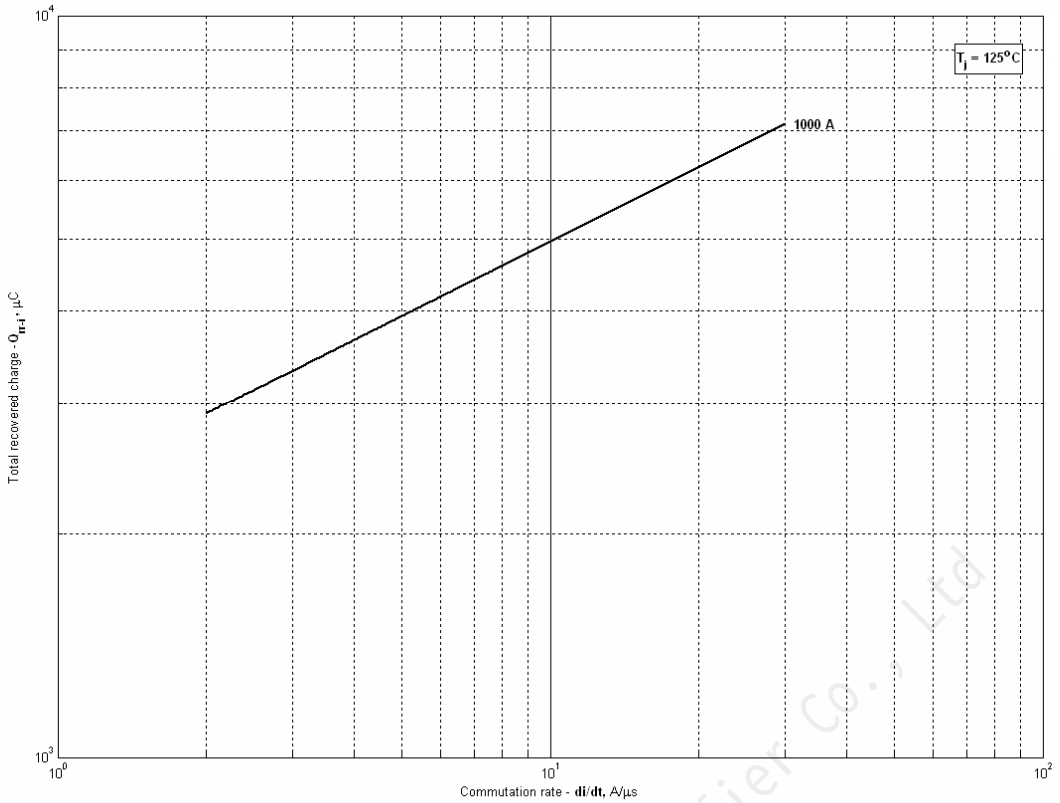


Fig 5 – Total recovered charge, Q_{rr-i} (integral)

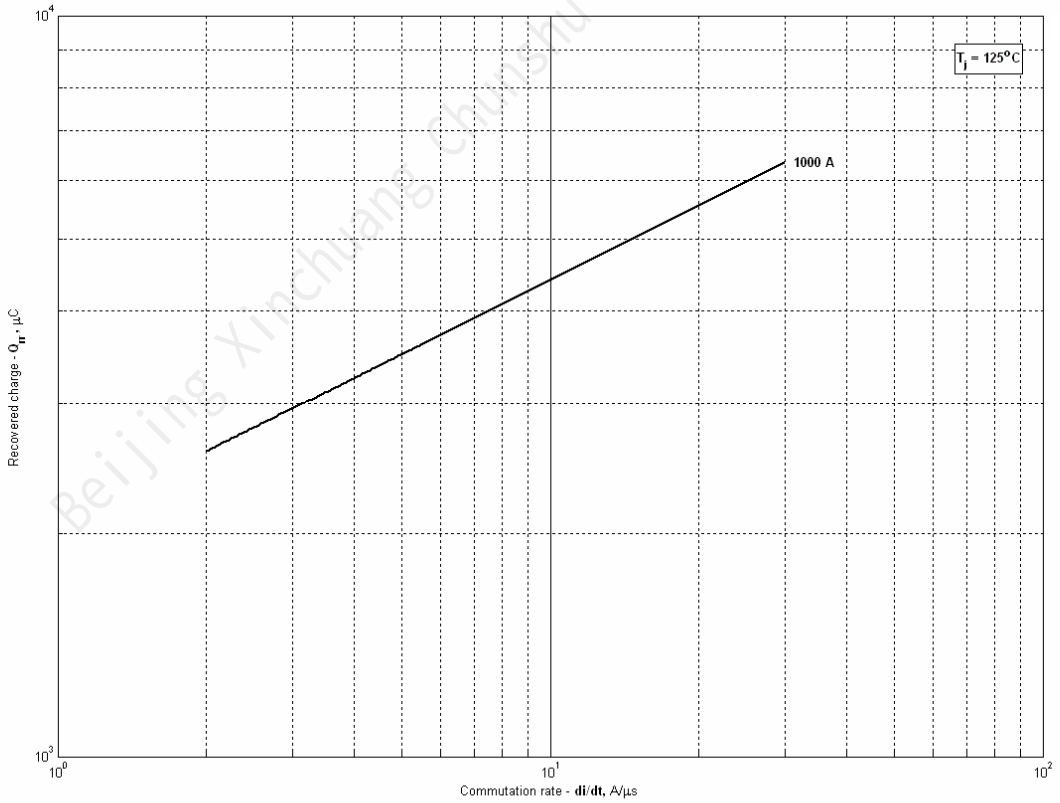


Fig 6 - Recovered charge, Q_{rr} (linear)

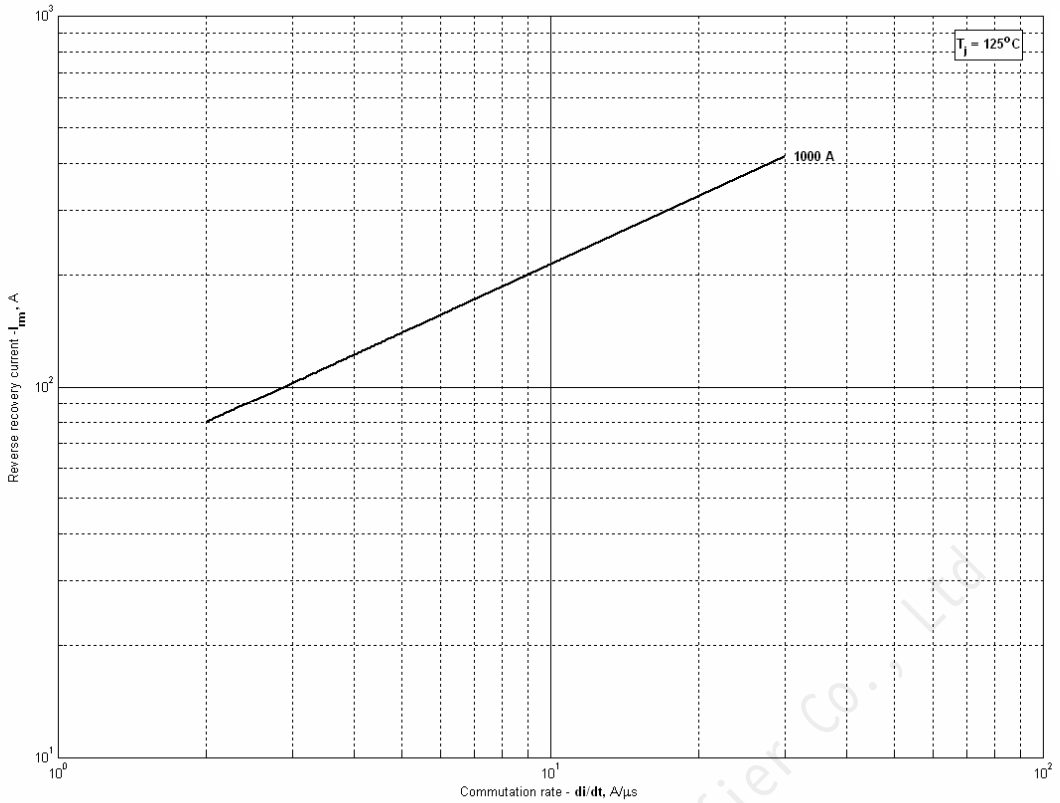


Fig 7 – Peak reverse recovery current, I_{rm}

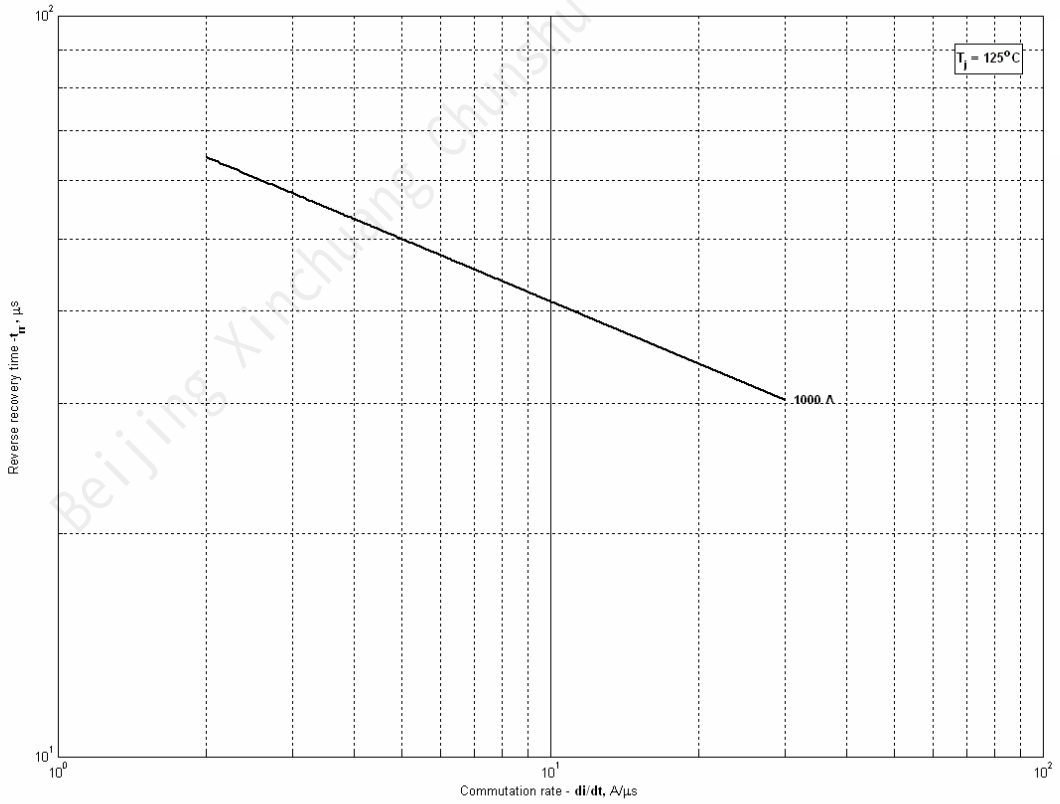


Fig 8 – Maximum recovery time, t_{rr} (linear)

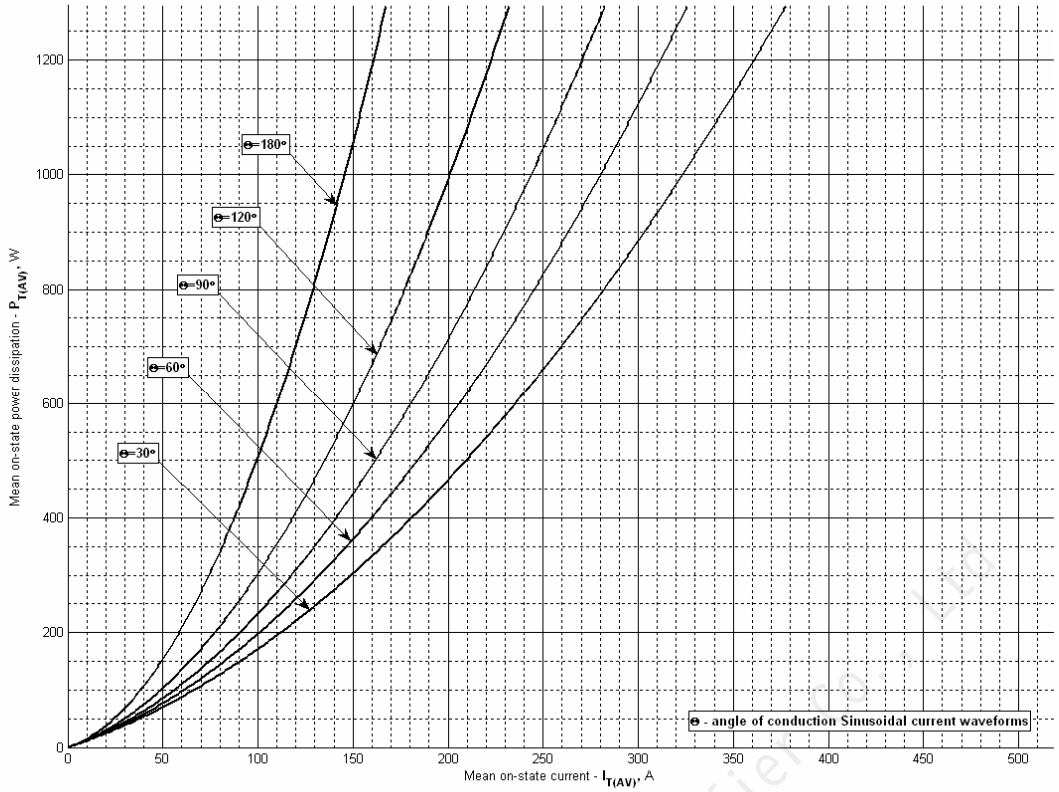


Fig 9 – On-state power loss (sinusoidal current waveforms)

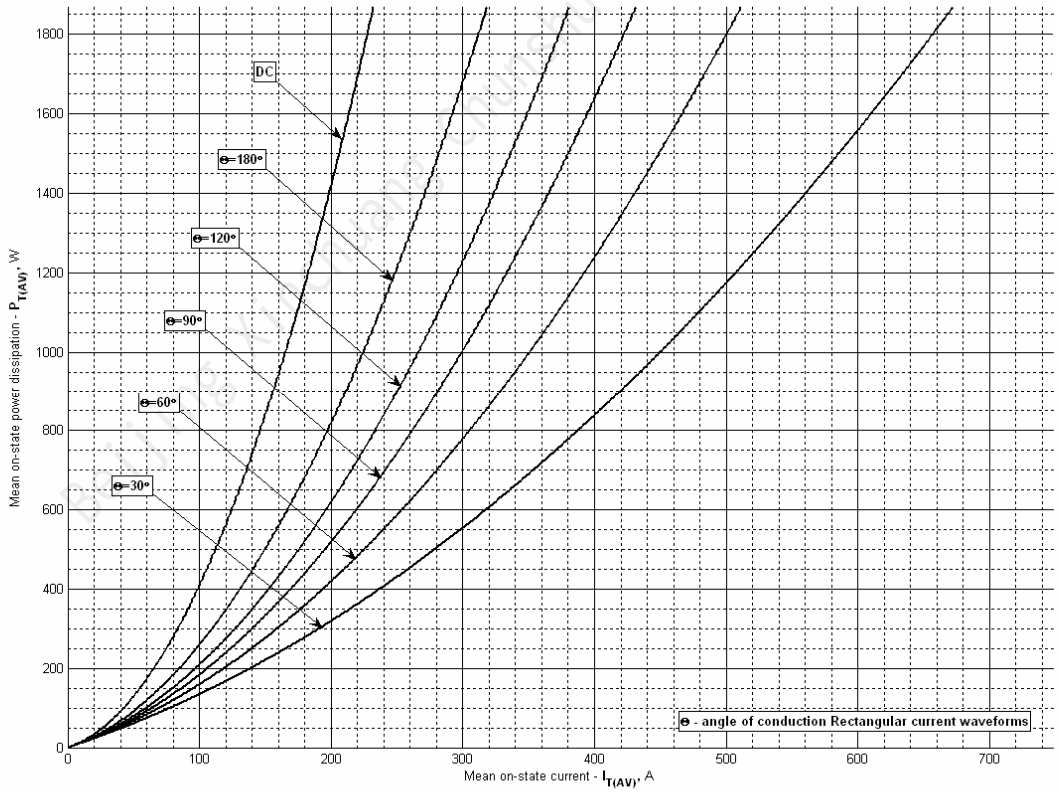


Fig 10 – On-state power loss (rectangular current waveforms)

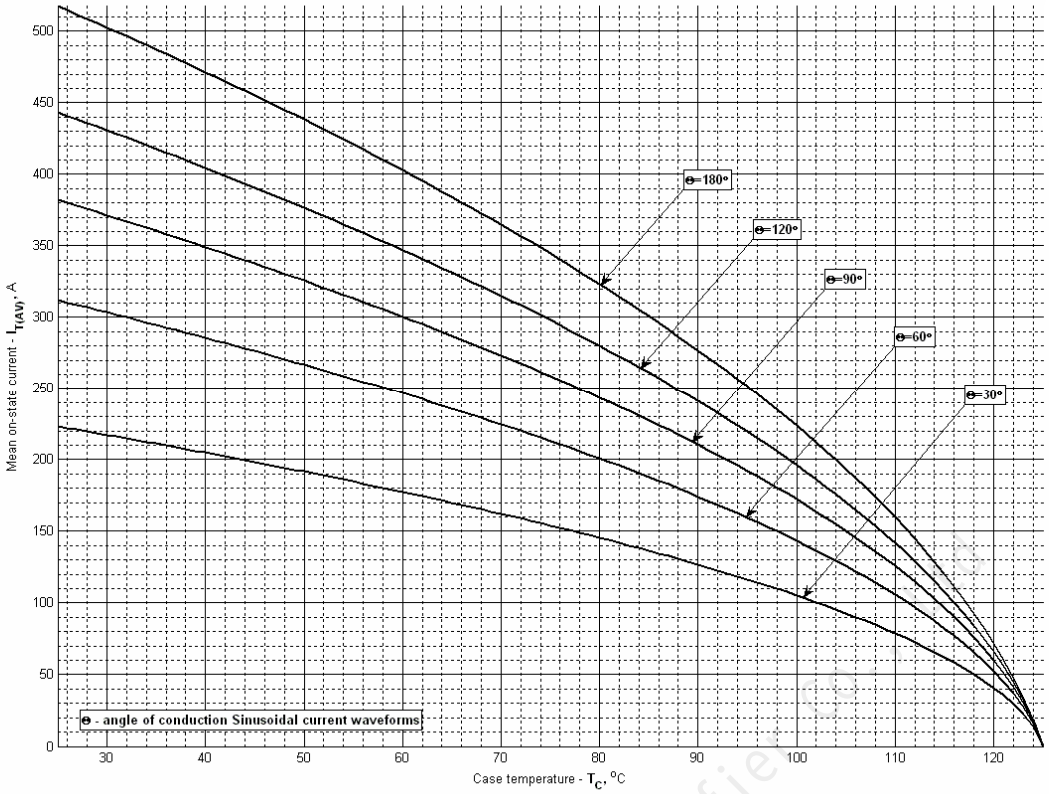


Fig 11 – Maximum case temperature DSC (sinusoidal current waveforms)

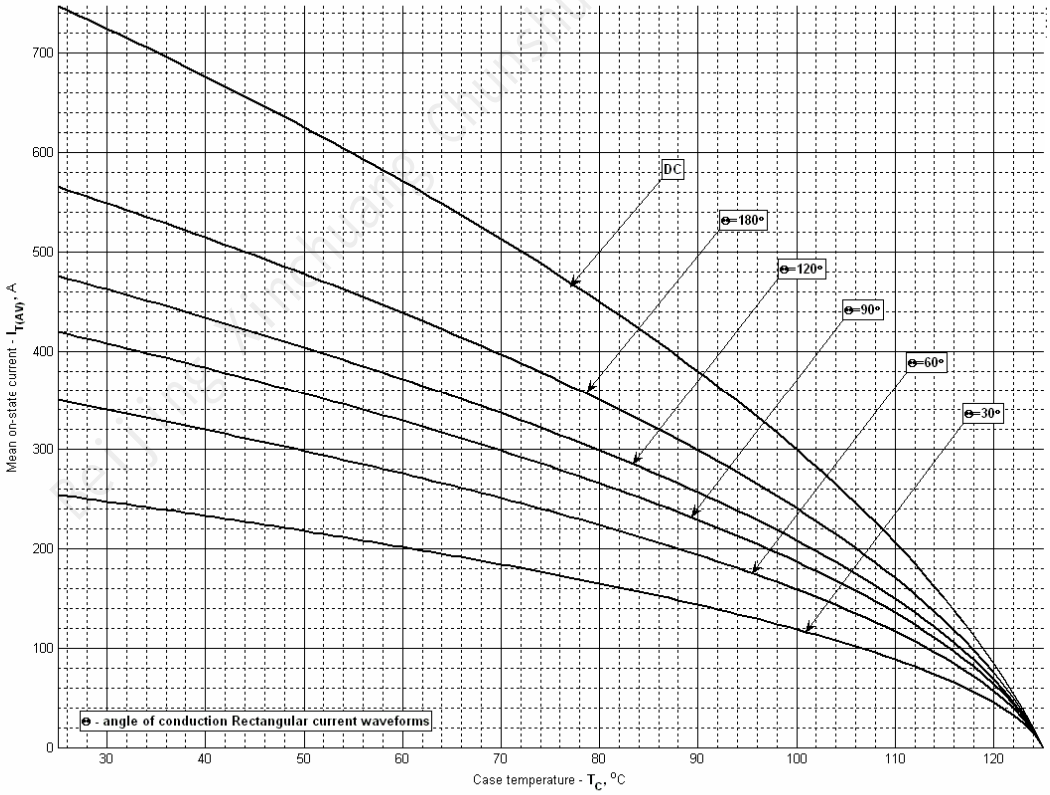


Fig 12 – Maximum case temperature DSC (rectangular current waveforms)

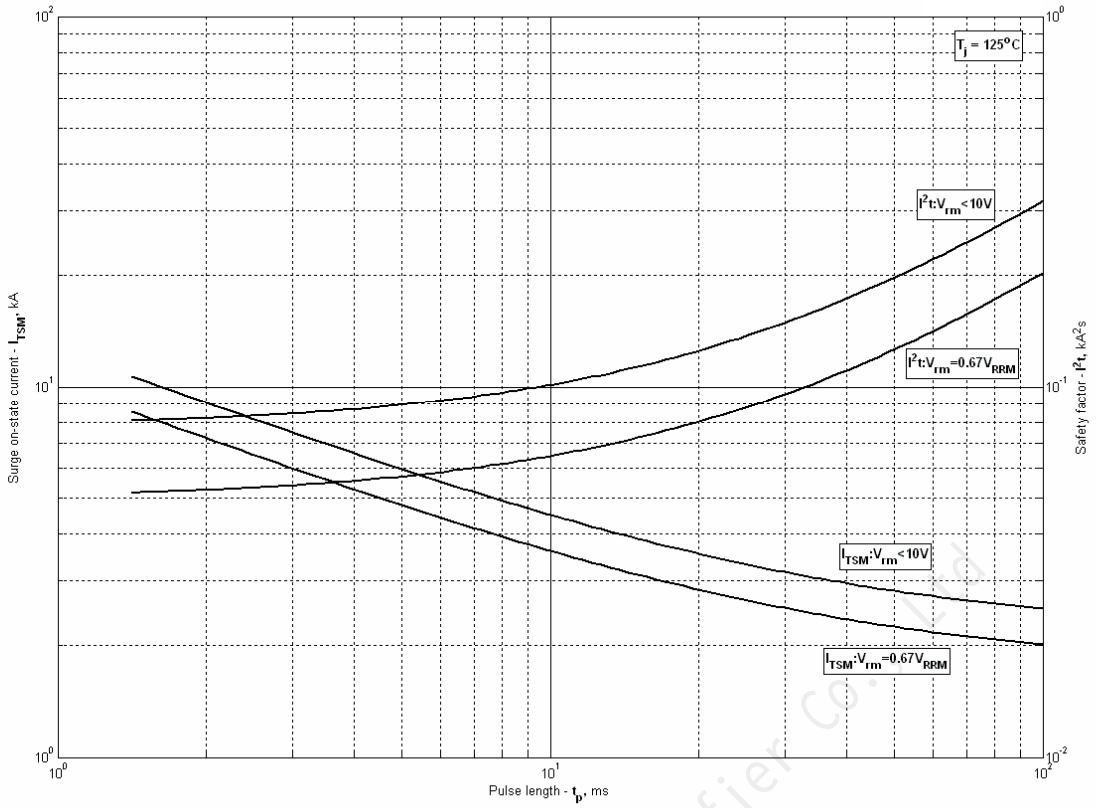


Fig 13 – Maximum surge and I^2t ratings

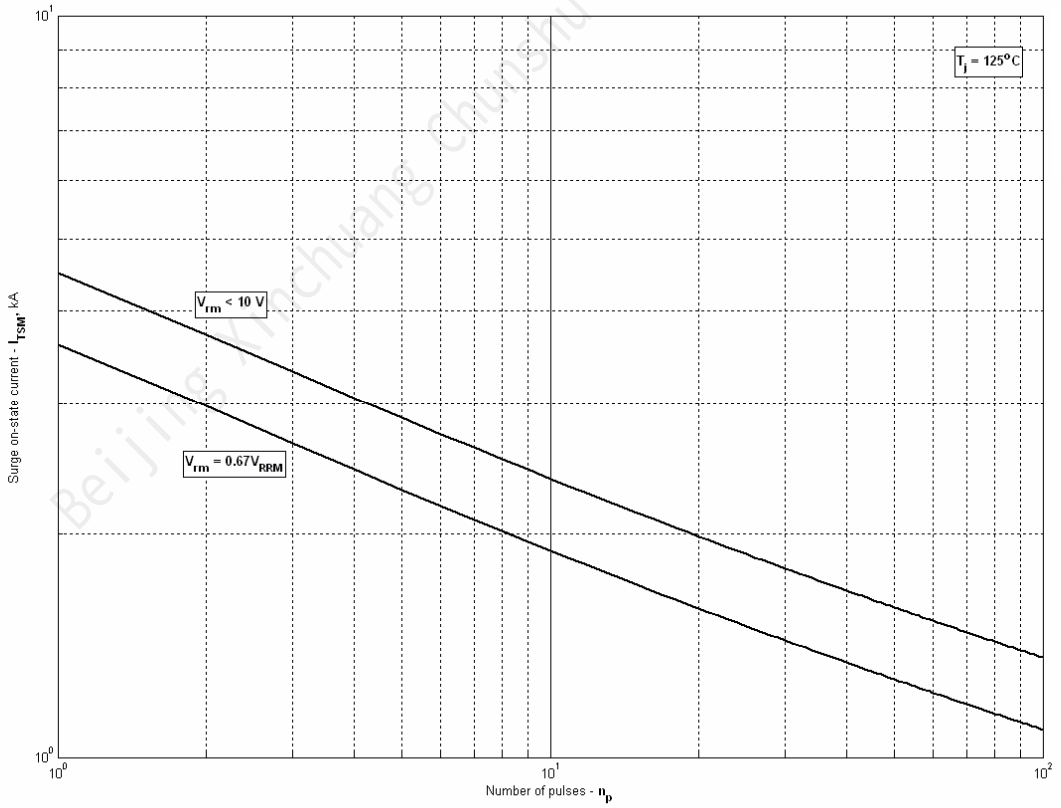


Fig 14 – Maximum surge ratings

